PNP/NPN Epitaxial Planar Silicon Transistors



2SB1202/2SD1802

High-Current Switching Applications

Applications

· Voltage regulators, relay drivers, lamp drivers, electrical equipment.

Features

- · Adoption of FBET, MBIT processes.
- · Large currrent capacity and wide ASO.
- \cdot Low collector-to-emitter saturation voltage.
- · Fast switching speed.
- Small and slim package making it easy to make 2SB1202/2SD1802-used sets smaller.

Package Dimensions

unit:mm





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- Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.
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():2SB1202

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(–)60	V
Collector-to-Emitter Voltage	VCEO		(–)50	V
Emitter-to-Base Voltage	VEBO		(–)6	V
Collector Current	۱ _C		(–)3	A
Collector Current (Pulse)	I _{CP}		(–)6	A
Collector Dissipation	PC		1	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings			
Parameter	Symbol	Conditions	min	typ	max	Unit	
Collector Cutoff Current	ICBO	V _{CB} =(-)40V, I _E =0			(–)1	μA	
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)1	μA	
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)100mA	100*		560*		
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)3A	35				
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)50mA		150		MHz	
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz		(39)25		pF	
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)2A, I _B =(-)100mA		0.19	0.5	V	
				(-0.35)	(-0.7)	V	
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)2A, I _B =(-)100mA		()0.94	(–)1.2	V	
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)10μA, I _E =0	(–)60			V	
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(–)50			V	
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(-)10μΑ, I _C =0	(–)6			V	
Turn-ON Time	ton	See specified Test Circuit		70		ns	
Storage Time	tstg	See specified Test Circuit		(450)		ns	
				650		ns	
Fall Time	tf	See specified Test Circuit		35		ns	

 \ast : The 2SB1202/2SD1802 are classified by 100mA h_{FE} as follows :

	100	R	200	140	S	280	200	Т	400	280	U	560	
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Switching Time Test Circuit



I C=10 I B1=-10 I B2=1A (For PNP, the polarity is reversed.) Unit (resistance : Ω, capacitance : F)







